Thyristor Modules

Liujing rectifier co., Ltd.

V_{RSM}	V_{RRM} V_{DRM}	I_{TRMS} =220A(maximum value for continous operation)		
V	V	I_{TAV} =130A(sin.180; Tc=87℃)		
900	800	SKKT 132/08E	SKKH 132/08E	
1300	1200	SKKT 132/12E	SKKH 132/12E	
1500	1400	SKKT 132/14E	SKKH 132/14E	
1700	1600	SKKT 132/16E	SKKH 132/16E	
1900	1800	SKKT 132/18E	SKKH 132/18E	

Symbol	Conditions	Values	Units
I_{TAV}	sin. 180; Tc = 85(100)℃;	137 (96)	A
V_{isol}	sin. 180; Tc = ℃		A
I_D	P3/180 ; Ta = 45℃; B2 / B6	77 / 100	A
	P3/180F; Ta = 35℃; B2 / B6	170 / 200	A
I_{RMS}	P3/180F; Ta = 35℃; W1 / W3	240 / 3*163	A
I_{TSM}	T_{vj} = 25℃; 10ms	4700	A
	T_{vj} = 125℃; 10ms	4000	A²S
i²t	T_{vj} = 25℃; 8，3 ...10ms	110000	A²S
	T_{vj} = 125℃; 8，3 ...10ms	80000	V
V_T	T_{vj} = 25℃; I_T=396A	max.1.8	V
$V_{T(TO)}$	T_{vj} = 125℃	max.1	mΩ
r_T	T_{vj} = 125℃	max.1.6	mA
I_{DD};I_{RD}	T_{vj} = 125℃; V_{RD}=V_{RRM} ; V_{DD}=V_{DRM}	max.40	μs
t_{gd}	T_{vj} = 25℃; I_G = 1A; di$_G$/dt = A/μs	1	μs
t_{gr}	V_D = 0.67*V_{DRM}	1	A/μs
$(di/dt)_{cr}$	T_{vj} = 125℃	max. 200	V/μs
$(dv/dt)_{cr}$	T_{vj} = 125℃	max. 1000	μs
t_q	T_{vj} = 125℃	250	mA
I_H	T_{vj} = 25℃ ; typ./max	150 / 400	mA
I_L	T_{vj} = 25℃ ; RG = 33Ω ; typ./max	300 / 1000	V
V_{GT}	T_{vj} = 25℃ ; d.c.	min. 2	mA
I_{GT}	T_{vj} = 25℃ ; d.c.	min. 150	V
V_{GD}	T_{vj} = 125℃ ; d.c.	max. 0.25	mA
I_{GD}	T_{vj} = 125 ℃ ; d.c.	max. 10	K/W
$R_{th(j-c)}$	cont.; per thyristor/per module	0.18 / 0.09	K/W
$R_{th(j-c)}$	sin. 180; per thyristor/per module	1.19 / 0.095	K/W
$R_{th(j-c)}$	rec. 120; per thyristor/per module	0.21 / 0.105	K/W
$R_{th(j-c)}$	per thyristor/per module	0.1 / 0.05	℃
T_{vj}		- 40...+ 125	℃
T_{stg}		- 40...+ 125	V~
V_{isol}	a. c. 50Hz; r.m.s. ; 1s/1min	3600/3000	Nm
M_s	to heatsink	5 ± 15%[1])	Nm
M_t	to terminal	5 ± 15%	m/s²
a		5 * 9.81	g
m	approx.	165	
Case	SKKT	LJ2	

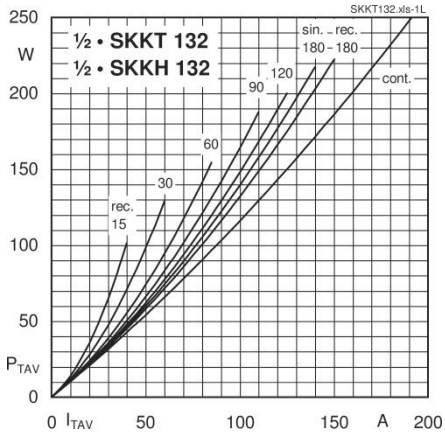


Fig. 1L Power dissipation per thyristor vs. on-state current

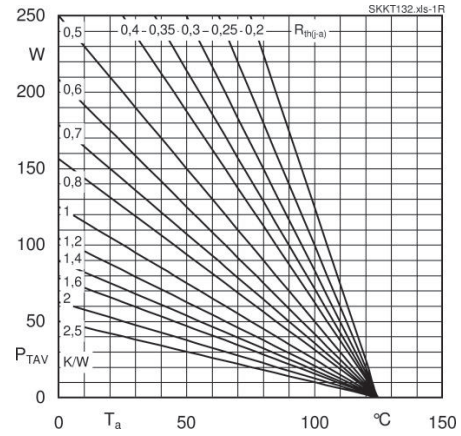


Fig. 1R Power dissipation per thyristor vs. ambient temp.

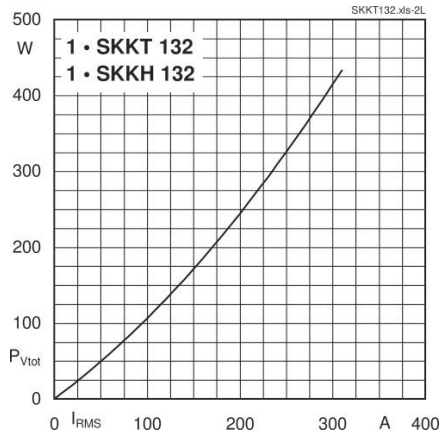


Fig. 2L Power dissipation per module vs. rms current

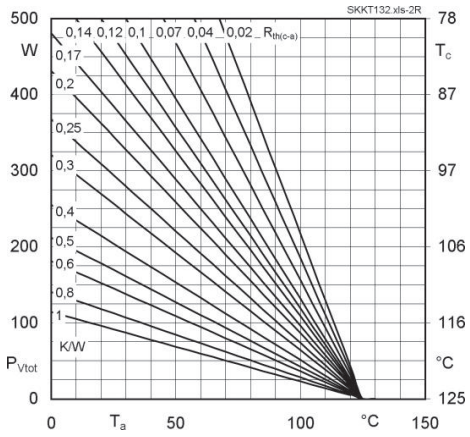


Fig. 2R Power dissipation per module vs. case temp.

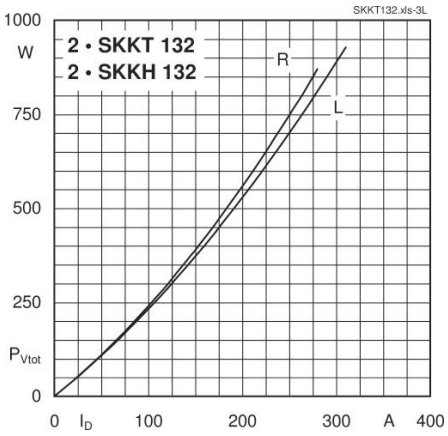


Fig. 3L Power dissipation of two modules vs. direct current

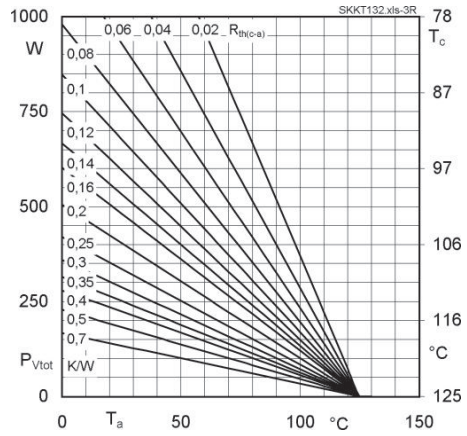


Fig. 3R Power dissipation of two modules vs. case temp.

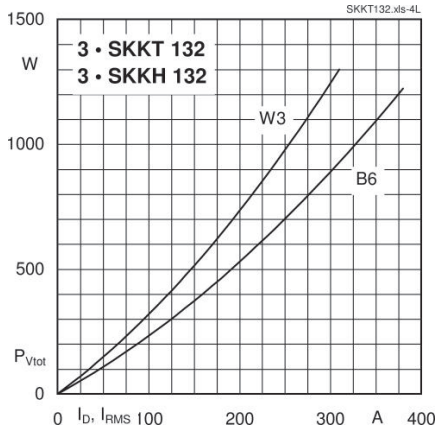


Fig. 4L Power dissipation of three modules vs. direct and rms current

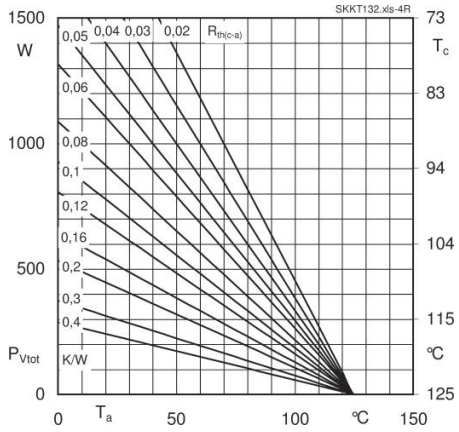


Fig. 4R Power dissipation of three modules vs. case temp.

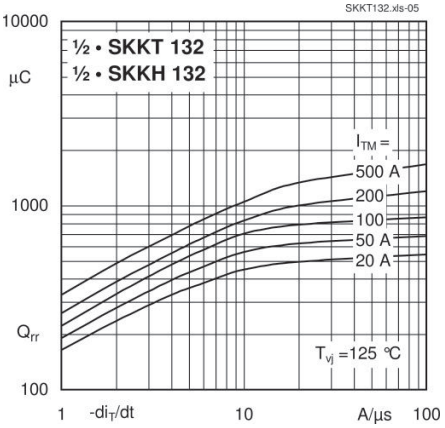


Fig. 5 Recovered charge vs. current decrease

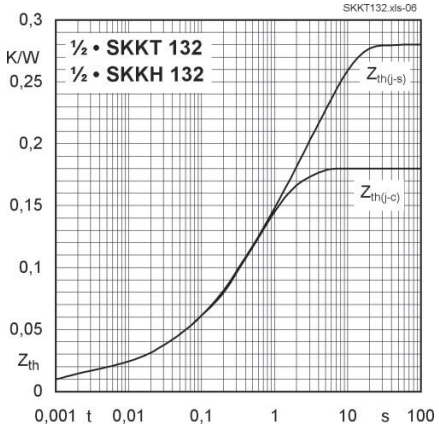


Fig. 6 Transient thermal impedance vs. time

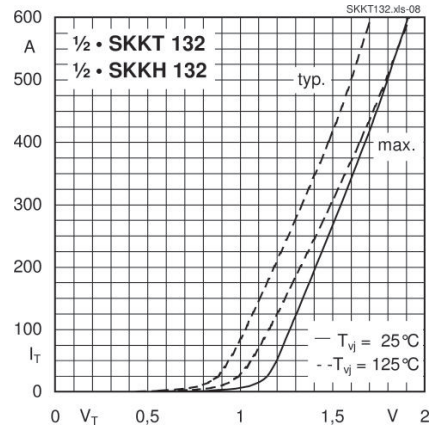


Fig. 7 On-state characteristics

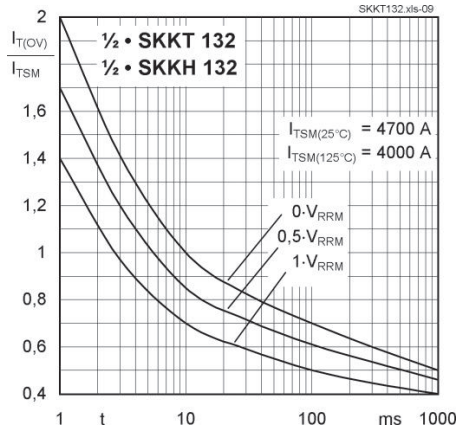
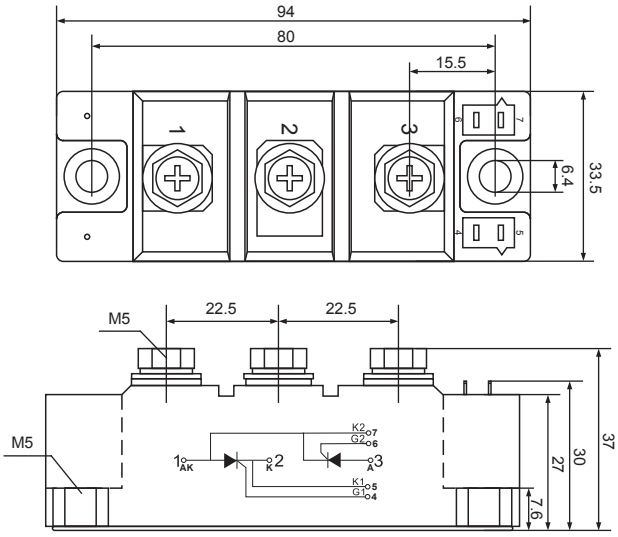


Fig. 8 Surge overload current vs. time



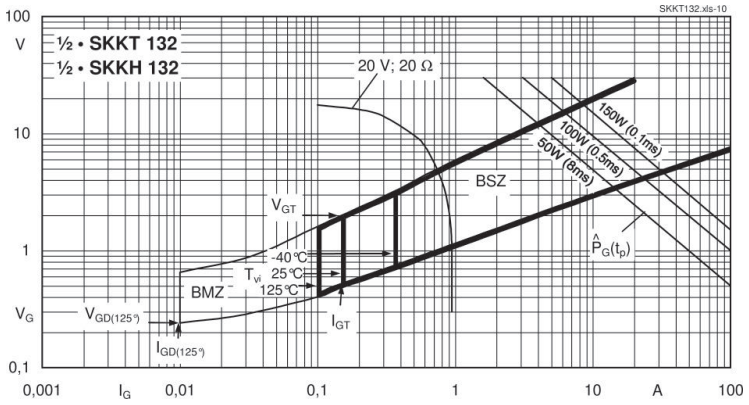


Fig. 9 Gate trigger characteristics

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